



WANSEMI
万芯半导体

WP3024

Enhancement Mode N+P-Channel Power MOSFET

TO-252-4L/N+PMOS/30V/ \pm 20V/1.7V/18A/9.5m Ω

-30V/ \pm 20V/-1.7V/-14A/22m Ω

Rev1.1

30V N+P-Channel MOSFET

1.Features

- ◆ High power and current handing capability
- ◆ Lead free product is acquired
- ◆ Fast switching
- ◆ Surface mount package

◆ N-Channel

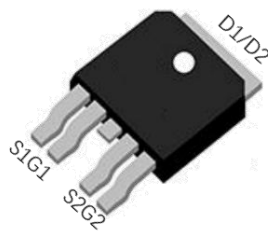
V _{DS}	R _{DS(on)} Typ.	I _D
30V	9.5mΩ @ 10V	18A
	14mΩ @ 4.5V	

◆ P-Channel

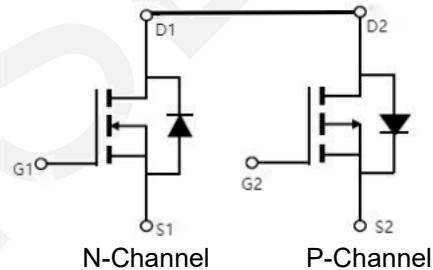
V _{DS}	R _{DS(on)} Typ.	I _D
-30V	22mΩ @ -10V	-14A
	30mΩ @ -4.5V	

2.Applications

- ◆ BLDC Motor driver
- ◆ PWM applications



TO-252-4L
Pin Description



Schematic Diagram

3.Package Marking and Ordering Information

Part no.	Marking	Package	PCS/Reel	PCS/CTN.
WP3024	WP3024	TO-252-4L	2,500	25,000

4.Absolute Max Ratings at Ta=25°C (Note1)

Parameter	Symbol	N-chanel	P-chanel	Units
Drain to Source Voltage	V _{DSS}	30	-30	V
Gate to Source Voltage	V _{GSS}	±20	±20	V
Drain Current (DC)	I _D	18	-14	A
Drain Current (Pulse), PW≤300μs	I _{DM}	50	-36	A
Total Dissipation	P _D	15.5	27	W
Avalanche Energy, Single Pulsed	EAS	72	56	mJ

Parameter	Symbol	N-channel	P-channel	Units
Junction Temperature	T_j	150	150	°C
Storage Temperature	T_{stg}	-55 to +150	-55 to +150	°C

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

5. Thermal Resistance Ratings (Note 2)

Parameter	Symbol	N-channel	P-channel	Unit
Maximum Junction-to-Ambient	$R_{\theta JA}$	39	29	°C/W

Note 2: When mounted on 1 inch square copper board $t \leq 10\text{sec}$ The value in any given application depends on the user's specific board design.

6. Electrical Characteristics at $T_a=25^\circ\text{C}$ (Note 3)

N-Channel

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	30	-	-	V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$	-	-	1	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_{DS}=250\mu\text{A}$	1.0	1.7	2.5	V
Static Drain to Source On-State Resistance	$R_{DS(on)}$	$I_D = 8\text{A}, V_{GS} = 10\text{V}$	-	9.5	13	$\text{m}\Omega$
		$I_D = 6\text{A}, V_{GS} = 4.5\text{V}$	-	14	20	$\text{m}\Omega$
Input Capacitance	C_{iss}	$V_{GS}=0\text{V},$ $V_{DS}=15\text{V},$ Frequency=1.0MHz	-	1011	-	pF
Output Capacitance	C_{oss}		-	142	-	pF
Reverse Transfer Capacitance	C_{rss}		-	119	-	pF
Turn-ON Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{V}$ $V_{GS} = 10\text{V}$ $R_L = 2.5\Omega$ $R_G=3\Omega$	-	5	-	ns
Rise Time	t_r		-	12	-	ns
Turn-OFF Delay Time	$t_{d(off)}$		-	19	-	ns
Fall Time	t_f		-	6	-	ns
Total Gate Charge	Q_g	$V_{DS} = 15\text{V},$ $V_{GS} = 10\text{V},$ $I_D = 6\text{A}$	-	9.5	-	nC
	Q_{gs}		-	2.0	-	nC
	Q_{gd}		-	1.9	-	nC
Diode Forward Voltage	V_{FSD}	$I_S = 8\text{A}, V_{GS} = 0\text{V}$	0.5	0.83	1.2	V

P-Channel

Note 3: Product parametric performance is indicated in the Electrical Characteristics for the listed test

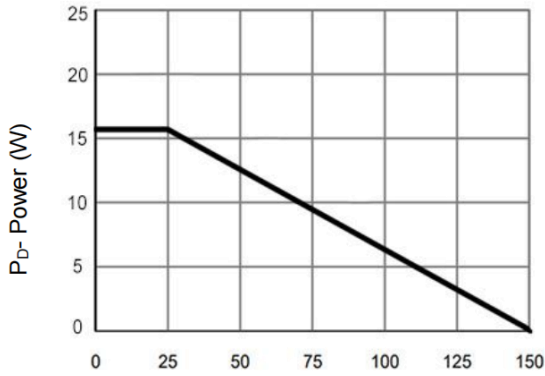
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -250\mu A, V_{GS} = 0V$	-30	-	-	V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$	-	-	-1	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_{DS}=-250\mu A$	-1.0	-1.7	-2.5	V
Static Drain to Source On-State Resistance	$R_{DS(on)}$	$I_D = -7A, V_{GS} = -10V$	-	22	29	m Ω
		$I_D = -5A, V_{GS} = -4.5V$	-	30	43	m Ω
Input Capacitance	C_{iss}	$V_{GS}=0V,$ $V_{DS}=-15V,$ Frequency=1.0MHz	-	1240	-	pF
Output Capacitance	C_{oss}		-	151	-	pF
Reverse Transfer Capacitance	C_{rss}		-	138	-	pF
Turn-ON Delay Time	$t_{d(on)}$	$V_{DD} = -15V$ $V_{GS} = -10V$ $R_{GEN} = 3\Omega,$ $R_L = 2.5\Omega,$	-	8	-	ns
Rise Time	t_r		-	30	-	ns
Turn-OFF Delay Time	$t_{d(off)}$		-	22	-	ns
Fall Time	t_f		-	26	-	ns
Total Gate Charge	Q_g	$V_{DS} = -15V,$	-	16.2	-	nC
	Q_{gs}	$V_{GS} = -10V,$	-	2.9	-	nC
	Q_{gd}	$I_D = -4A$	-	3.6	-	nC
Diode Forward Voltage	V_{FSD}	$I_S = -7A, V_{GS} = 0V$	-0.5	-0.87	-1.2	V

conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



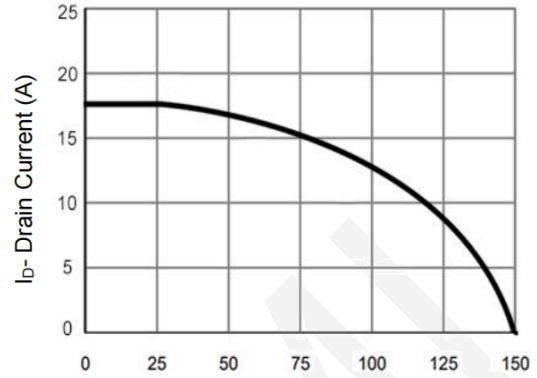
7. Typical electrical and thermal characteristics

N-Channel



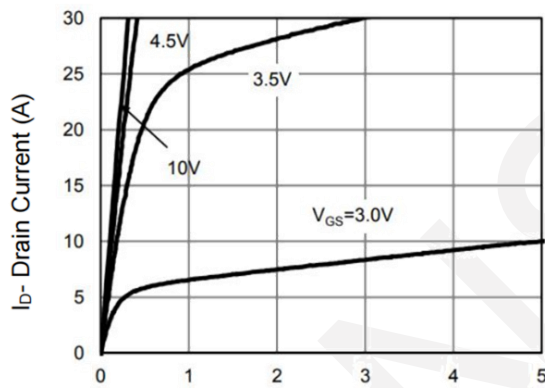
T_J-Junction Temperature (°C)

Power De-rating



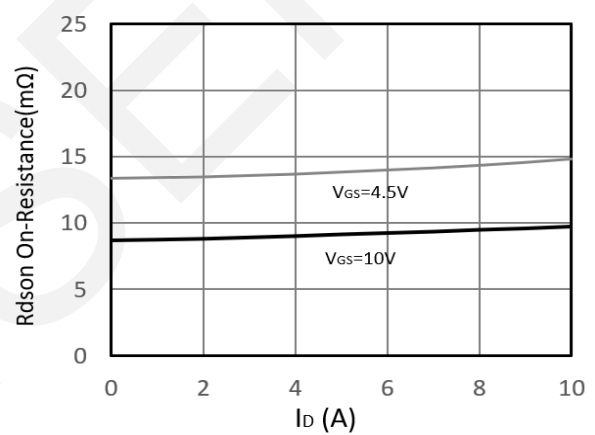
T_J-Junction Temperature (°C)

Drain Current

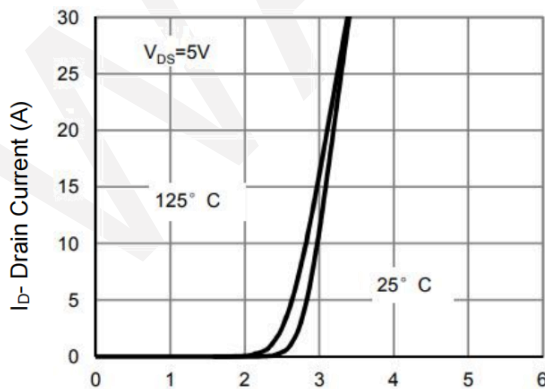


V_{DS} Drain-Source Voltage (V)

Output Characteristics

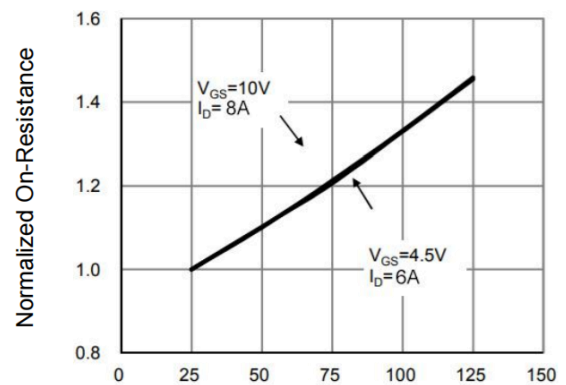


Rdson vs Drain Current



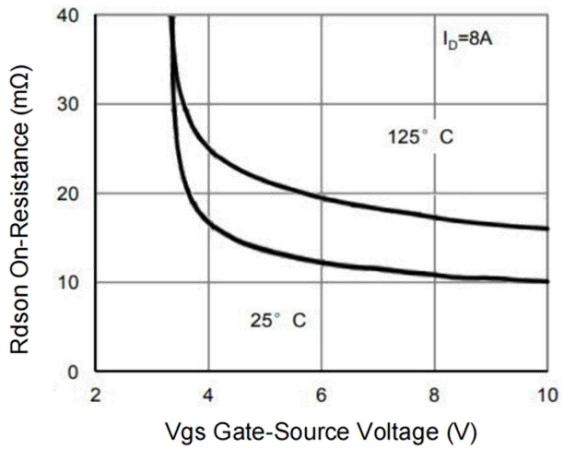
V_{GS} Gate-Source Voltage (V)

Transfer Characteristics

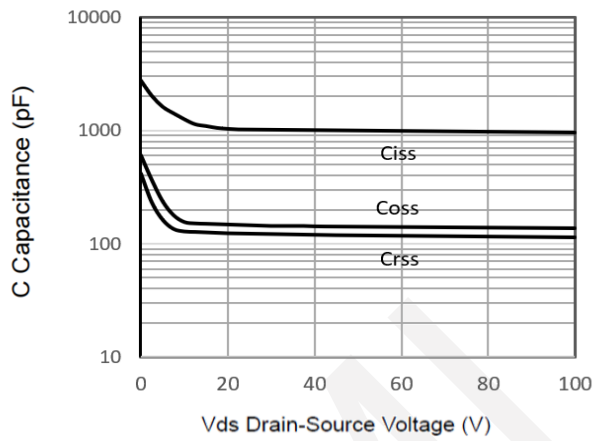


T_J-Junction Temperature(°C)

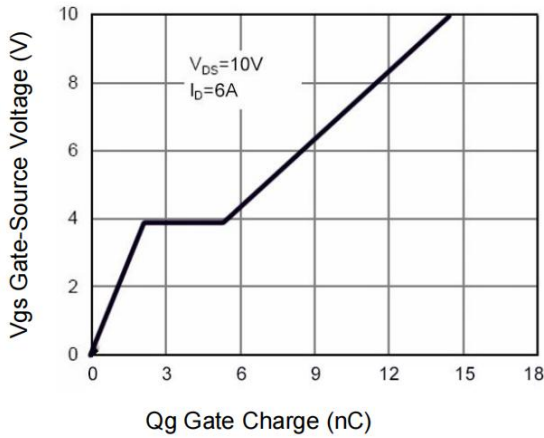
Rdson vs Junction Temperature



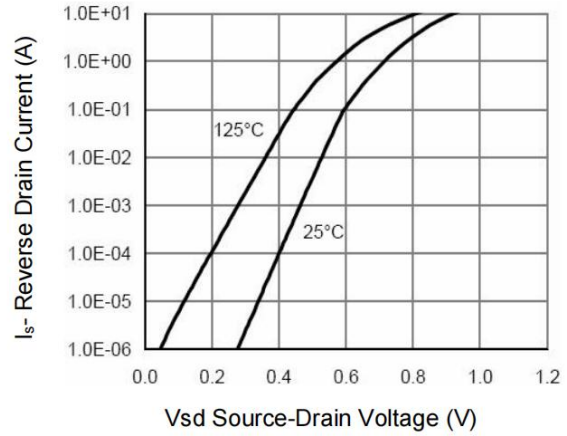
Rdson vs Vgs



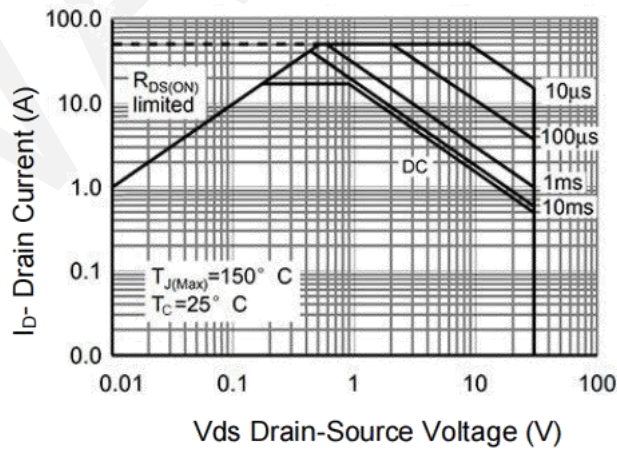
Capacitance vs Vds



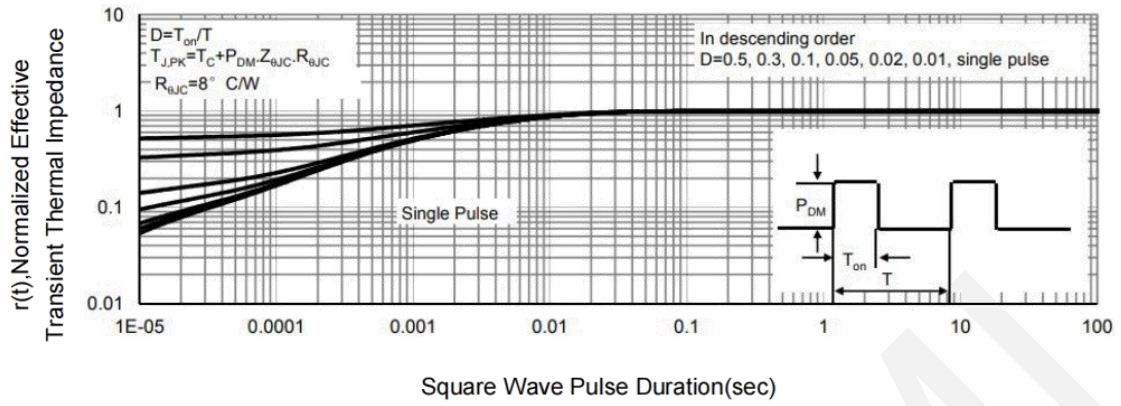
Gate Charge



Source- Drain Diode Forward



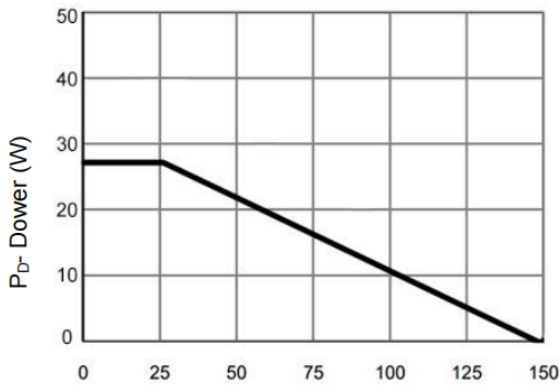
Safe Operating Area



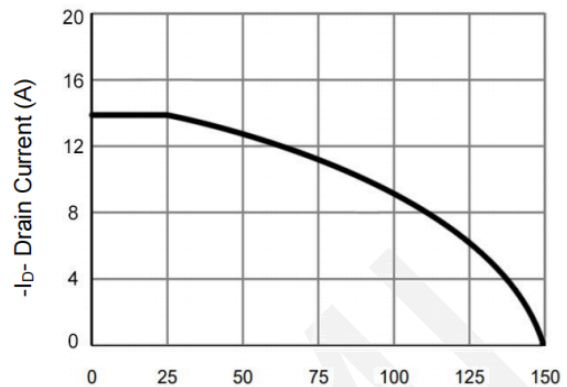
Normalized Maximum Transient Thermal Impedance



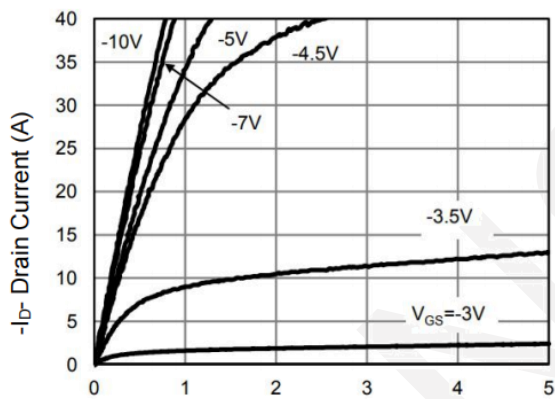
P-Channel



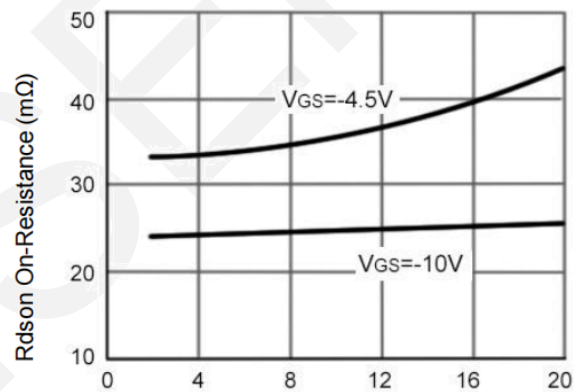
T_J-Junction Temperature (°C)
Power De-rating



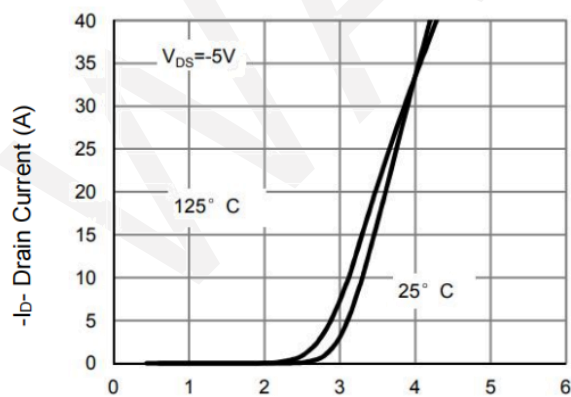
T_J-Junction Temperature (°C)
Drain Current



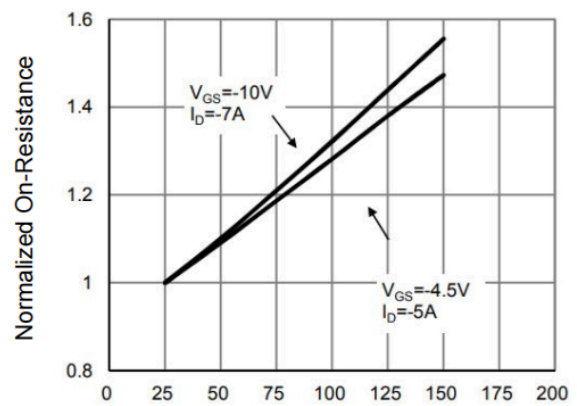
-V_{DS} Drain-Source Voltage (V)
Output Characteristics



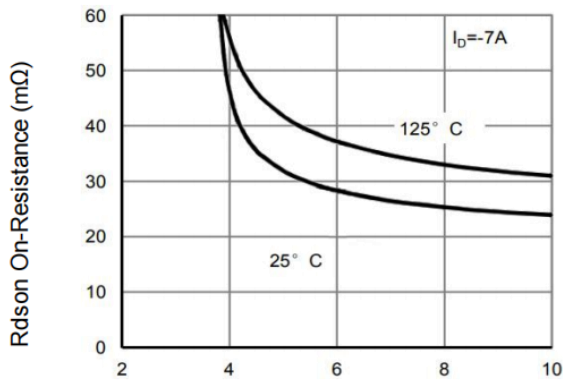
-I_D Drain Current (A)
Rdson vs Drain Current



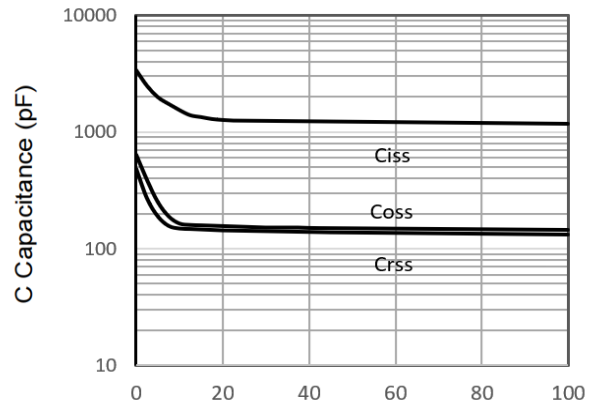
-V_{GS} Gate-Source Voltage (V)
Transfer Characteristics



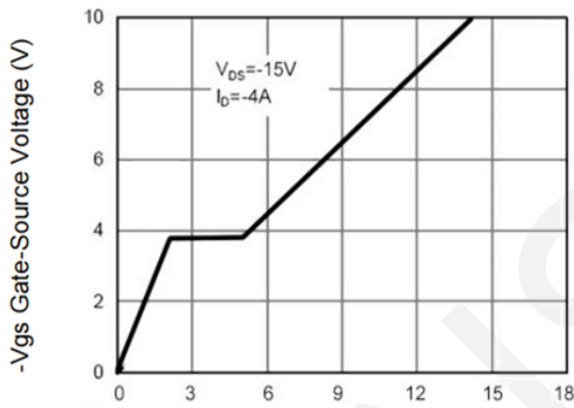
T_J-Junction Temperature(°C)
Rdson vs Junction Temperature



-Vgs Gate-Source Voltage (V)
Rdson vs Vgs

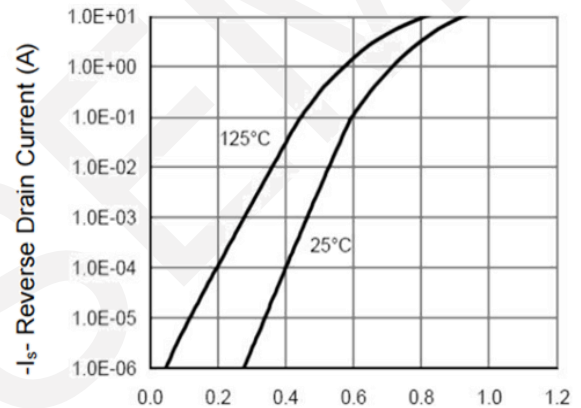


Vds Drain-Source Voltage (V)
Capacitance vs Vds



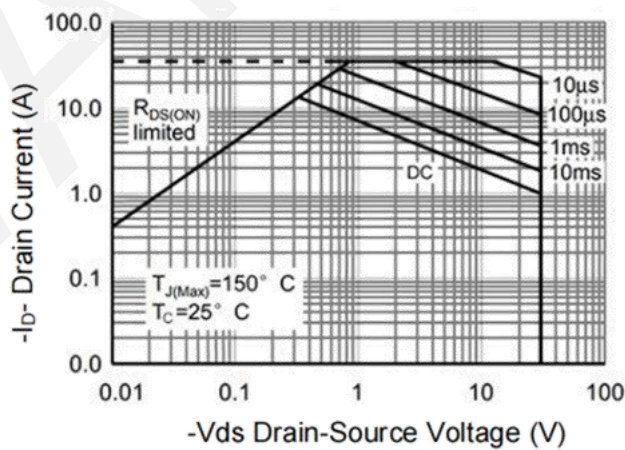
Qg Gate Charge (nC)

Gate Charge

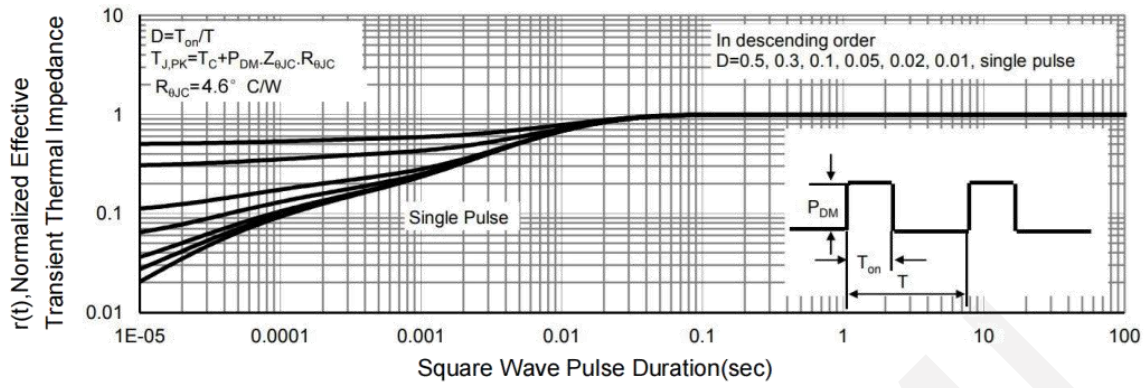


-Vsd Source-Drain Voltage (V)

Source- Drain Diode Forward



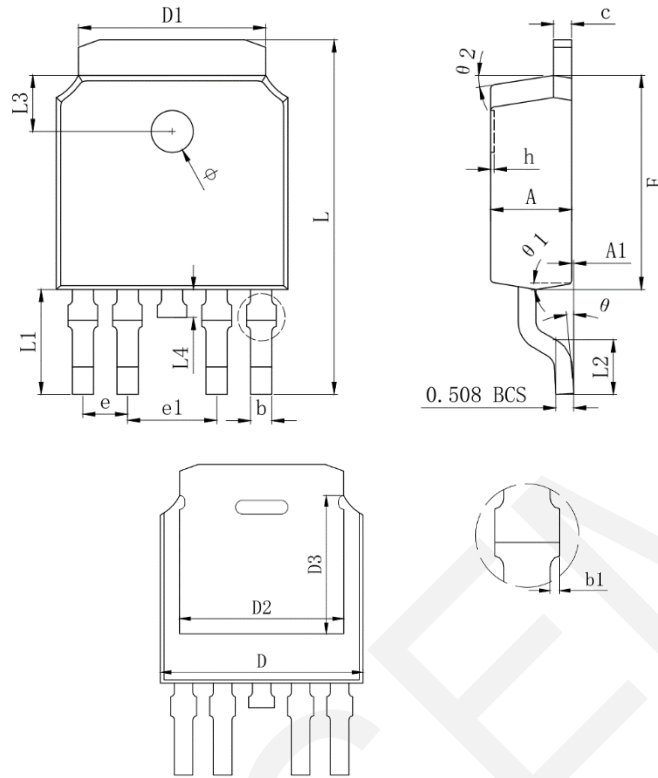
Safe Operating Area



Normalized Maximum Transient Thermal Impedance



8.Package Dimensions



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	2.200	2.300	2.400
A1	0.000		0.127
b	0.550	0.600	0.650
b1	0.000		0.120
c (电镀后)	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334 REF		
D2	5.346 REF		
D3	4.490 REF		
E	6.000	6.100	6.200
e	1.270 TYP		
e1	2.540 TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.988 REF		
L2	1.400	1.550	1.700
L3	1.600 REF		
L4	0.700	0.800	0.900
ϕ	1.100	1.200	1.300
θ	0°		8°
$\theta 1$	9° TYP		
$\theta 2$	9° TYP		

9. Important Notice

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